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FAIRCHILD

SEMICONDUCTOR

November 2013

FQD2N80

N-Channel QFET® MOSFET

800 V, 1.8 A, 6.3 Ω

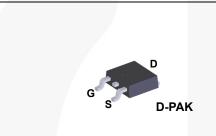
Description

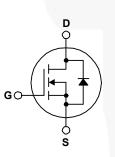
This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance . Low Crss (Typ. 5.5 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- 1.8 A, 800 V, $R_{DS(on)}$ = 6.3 Ω (Max.) @ V_{GS} = 10 V, I_D = 0.9 A
- Low Gate Charge (Typ. 12 nC)

- · RoHS Compliant





Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

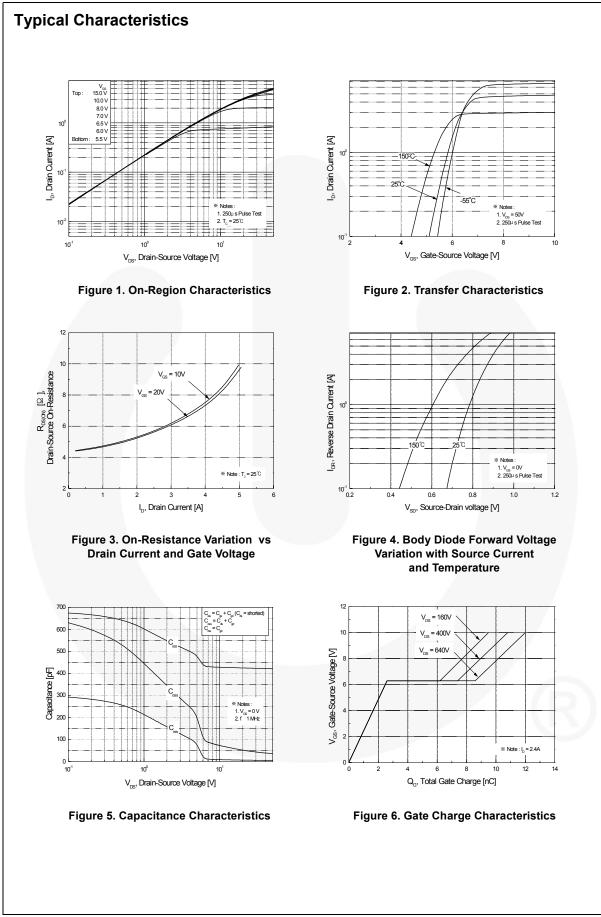
Symbol	Parameter		FQD2N80TM	Unit
V _{DSS}	Drain-Source Voltage		800	V
ID	Drain Current - Continuous (T _C = 25°C)		1.8	А
	- Continuous (T _C = 100°C)		1.14	A
I _{DM}	Drain Current - Pulsed (No	ote 1)	7.2	A
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy (No	ote 2)	180	mJ
I _{AR}	Avalanche Current (No	ote 1)	1.8	A
E _{AR}	Repetitive Avalanche Energy (No	ote 1)	5.0	mJ
dv/dt	Peak Diode Recovery dv/dt (No	ote 3)	4.0	V/ns
P _D	Power Dissipation (T _A = 25°C) *		2.5	W
	Power Dissipation (T _C = 25°C)		50	W
	- Derate above 25°C		0.4	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C

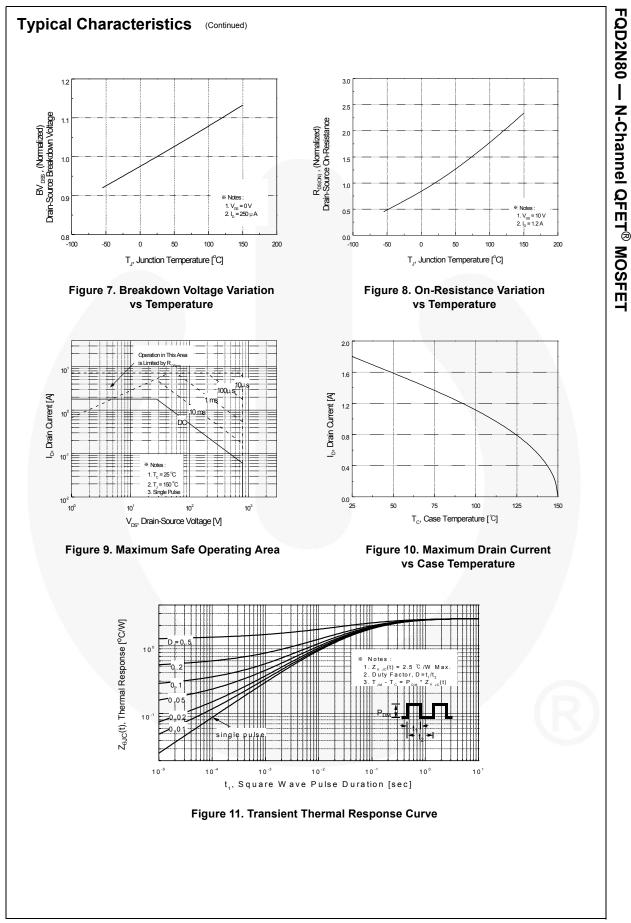
Thermal Characteristics

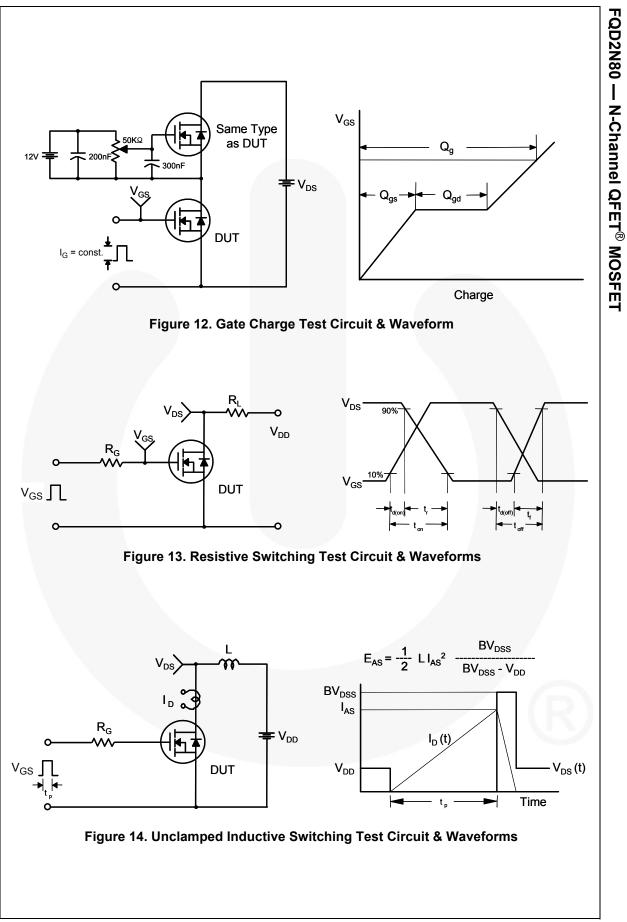
Symbol	Parameter	FQD2N80TM	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	2.5	
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	

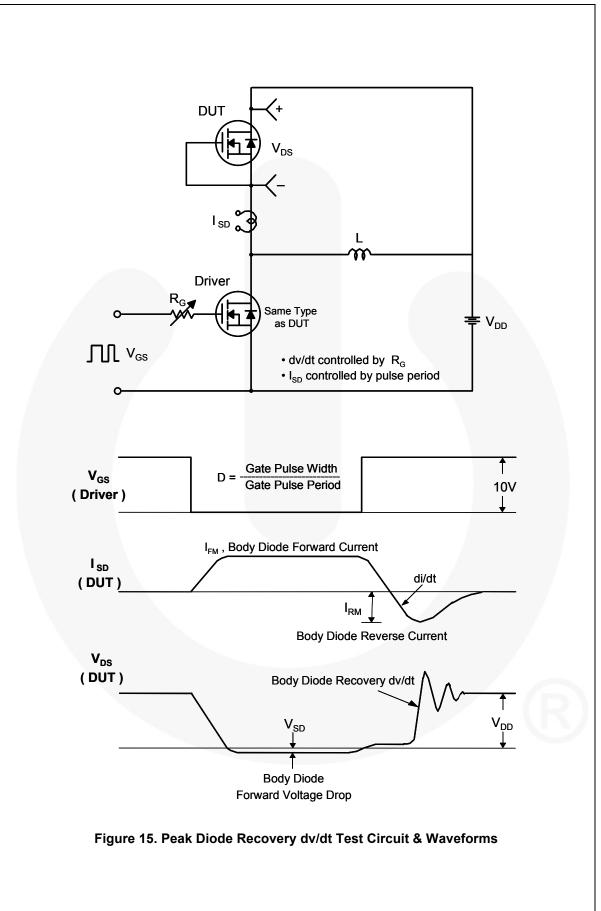
OTM FQD2N80 Al Characteristics Parameter Acteristics Drain-Source Breakdown Voltage Temperat	T _C = 25°C		Tape and Reel	330	mm Min.	16 m	m : Max.	2500 units
Parameter acteristics Drain-Source Breakdown Volt		Т			Min.	Тур.	Max.	Unit
acteristics Drain-Source Breakdown Vol	lage		est Conditions		Min.	Тур.	Max.	Unit
Drain-Source Breakdown Vol	tage							1
Drain-Source Breakdown Vol	tage							
		$V_{GS} = 0$	/, I _D = 250 μA		800			V
	ture							
Coefficient	.uro	$I_D = 250 \ \mu$ A, Referenced to 25° C			0.9		V/°C	
Zara Cata Valtaga Drain Current		V _{DS} = 800 V, V _{GS} = 0 V				10	μA	
Leio Gale Vollage Dialii Cuir	ent	V _{DS} = 640 V, T _C = 125°C					100	μA
Sate-Body Leakage Current,	Forward	V _{GS} = 30	V, V _{DS} = 0 V				100	nA
Gate-Body Leakage Current,	Reverse	V _{GS} = -30	0 V, V _{DS} = 0 V				-100	nA
acteristics								
Gate Threshold Voltage		V _{DS} = V _G	_{sS} , I _D = 250 μA	_	3.0		5.0	V
Static Drain-Source Dn-Resistance	_	V _{GS} =10	V, I _D =0.9 A			4.9	6.3	Ω
Forward Transconductance		V _{DS} = 50	V, I _D = 0.9 A			2.4		S
Characteriation		1				ļ		
						125	550	pF
	_						pF	
		f = 1.0 MH	HZ					pF
Furn-On Delay Time Furn-On Rise Time	_					12 30	35 70	ns ns
Turn-Off Delay Time		_		(Note 1)		25	60	ns
				(NOLE 4)		28	65	ns
0		V _{DS} = 64	0 V, I _D = 2.4 A,				15	nC
Sate-Source Charge		V _{GS} = 10	V _{GS} = 10 V			2.6		nC
Gate-Drain Charge				(Note 4)		6.0		nC
urce Diode Character	istics ar	nd Maxin	num Ratings					
Maximum Continuous Drain-S	Source Dic	ode Forward	d Current				1.8	Α
							7.2	Α
Drain-Source Diode Forward	Voltage						1.4	V
Reverse Recovery Time			-			480		ns
Reverse Recovery Charge		dI _F / dt =	100 A/μs			2.0		μC
	Gate-Body Leakage Current, Gate-Body Leakage Current, Gate-Body Leakage Current, Gate-Body Leakage Current, Gate-Body Leakage Current, Gate-Body Leakage Current, Gate Threshold Voltage Static Drain-Source Dn-Resistance Forward Transconductance Characteristics nput Capacitance Output Capacitance Reverse Transfer Capacitance Characteristics Furn-On Delay Time Furn-On Rise Time Furn-On Rise Time Furn-Off Fall Time Fotal Gate Charge Gate-Source Charge Gate-Source Charge Gate-Drain Charge Urce Diode Character Maximum Continuous Drain-Source Drain-Source Diode Forward	Gate Threshold Voltage Gate Threshold Voltage Gate Threshold Voltage Gate Threshold Voltage Characteristics Input Capacitance Cutput Capacitance Reverse Transfer Capacitance G Characteristics Ifurn-On Delay Time Ifurn-On Rise Time Ifurn-Off Delay Time Ifurn-Off Fall Time Ifotal Gate Charge Gate-Source Charge Gate-Drain Charge Unce Diode Characteristics Maximum Continuous Drain-Source Diode Forward Voltage Drain-Source Diode 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Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{ A}$ Static Drain-Source $V_{DS} = 10 \text{ V}, I_D = 0.9 \text{ A}$ On-Resistance $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ Forward Transconductance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_f = 1.0 \text{ MHz}$ Forward Transconductance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_f = 1.0 \text{ MHz}$ Reverse Transfer Capacitance $V_{DD} = 400 \text{ V}, I_D = 2.4 \text{ A}, R_G = 25 \Omega$ furn-On Rise Time $V_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, R_G = 25 \Omega$ furn-Off Delay Time $V_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, N_G = 10 \text{ V}$ Gate-Source Charge $V_{DS} = 10 \text{ V}$ Gate-Source Charge $V_{CS} = 10 \text{ V}$ Gate-Drain Charge $V_{GS} = 10 \text{ V}$ Maximum Continuous Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentTrain-Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_S = 1.8 \text{ A}$	Terro Gate Voltage Drain Current $V_{DS} = 640 \text{ V}, T_C = 125^{\circ}\text{C}$ Gate-Body Leakage Current, Forward $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ Gate Threshold Voltage $V_{DS} = 10 \text{ V}, I_D = 0.9 \text{ A}$ Characteristics $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ Characteristics $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ Characteristics $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$ Putput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, f = 1.0 \text{ MHz}$ Reverse Transfer Capacitance $V_{DD} = 400 \text{ V}, I_D = 2.4 \text{ A}, R_G = 25 \Omega$ Turn-On Delay Time $V_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, N_{GS} = 10 \text{ V}$ Turn-Off Fall Time $V_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, N_{GS} = 10 \text{ V}$ Total Gate Charge $V_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, N_{GS} = 10 \text{ V}$ Gate-Drain Charge $V_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, N_{GS} = 10 \text{ V}$ Maximum Continuous Drain-Source Diode Forward CurrentMaximum Continuous Drain-Source Diode Forward CurrentMaximum Continuous Drain-Source Diode Forward CurrentMaximum Pulsed Drain-Source Diode Forward CurrentOrain-Source Diode Forward Voltage $V_{GS} = 0 \text{ V}, I_S = 1.8 \text{ A}$	Terror Gate Voltage Drain Current $V_{DS} = 640 \text{ V}, T_C = 125^\circ \text{C}$ Gate-Body Leakage Current, Forward $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Cteristics $V_{GS} = 10 \text{ V}, I_D = 250 \mu \text{ A}$ 3.0Static Drain-Source $V_{GS} = 10 \text{ V}, I_D = 0.9 \text{ A}$ On-Resistance $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ Forward Transconductance $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ CharacteristicsDuput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ CharacteristicsCurn-On Delay TimeV_{DD} = 400 \text{ V}, I_D = 2.4 \text{ A},Turn-Off Delay TimeV_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A},Turn-Off Fall TimeV_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A},Total Gate ChargeV_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A},Gate-Source ChargeV_{DS} = 10 \text{ V}Gate-Source ChargeV_{DS} = 10 \text{ V}Gate-Drain ChargeV_{OS} = 00 \text{ V}, I_D = 2.4 \text{ A},Maximum Continuous Drain-Source Diode Forward Current	Terro Gate Voltage Drain Current $V_{DS} = 640 \text{ V}, T_{C} = 125^{\circ}\text{C}$ Gate-Body Leakage Current, Forward $V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ Gate-Body Leakage Current, Reverse $V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$ acteristicsGate Threshold Voltage $V_{DS} = V_{GS}, I_D = 250 \mu \text{ A}$ 3.0Static Drain-Source $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ 4.9On-Resistance $V_{DS} = 50 \text{ V}, I_D = 0.9 \text{ A}$ 2.4Characteristicsnput Capacitance $V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V}, I_S = 0 \text{ V}, I_S = 1.0 \text{ MHz}$ 425Characteristicsf = 1.0 MHz4.54.5Severse Transfer Capacitance $V_{DD} = 400 \text{ V}, I_D = 2.4 \text{ A}, I_S =30furm-On Delay TimeV_{DS} = 640 \text{ V}, I_D = 2.4 \text{ A}, I_S =2.6furm-Off Delay TimeV_{OS} = 10 \text{ V}122.6furm-Off Fall TimeV_{OS} = 10 \text{ V}, I_D = 2.4 \text{ A}, I_S =122.6furm-Off Delay TimeV_{OS} = 10 \text{ V}, I_D = 2.4 \text{ A}, I_S =122.6furm-Off Fall TimeV_{OS} = 10 \text{ V}, I_D = 2.4 \text{ A}, I_S =122.6Gate-Source ChargeV_{OS} = 10 $	$\begin{tabular}{ c c c c c } \hline V_{DS} &= 640 \ V, \ T_C &= 125^\circ C & & & 100 \\ \hline V_{DS} &= 640 \ V, \ T_C &= 125^\circ C & & & 100 \\ \hline \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$

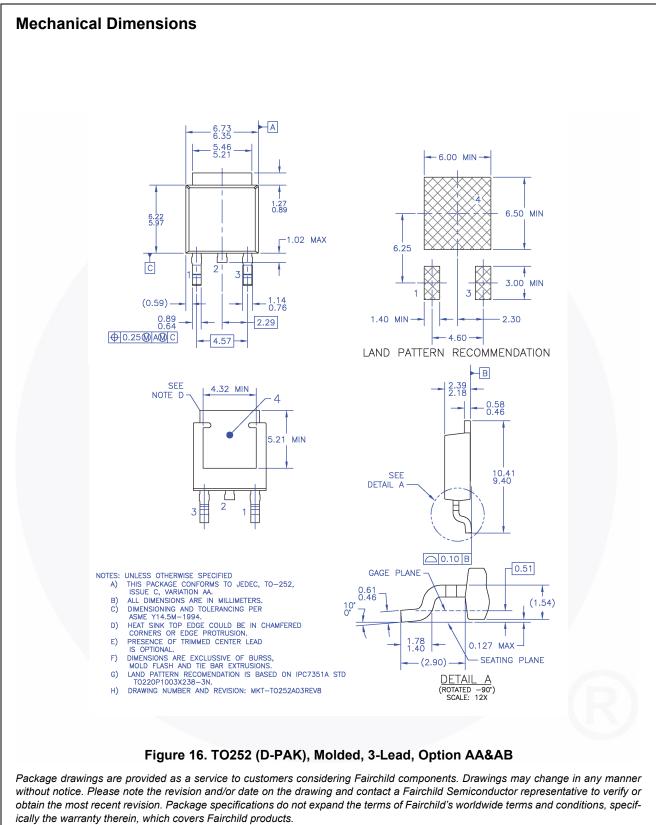
FQD2N80 — N-Channel QFET[®] MOSFET











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Rev.					

QD2N80

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N-Channel QFET[®] MOSFET

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